ULTRAFAST LASER-INDUCED PHASE TRANSITIONS IN SEMICONDUCTORS

Eli Glezer
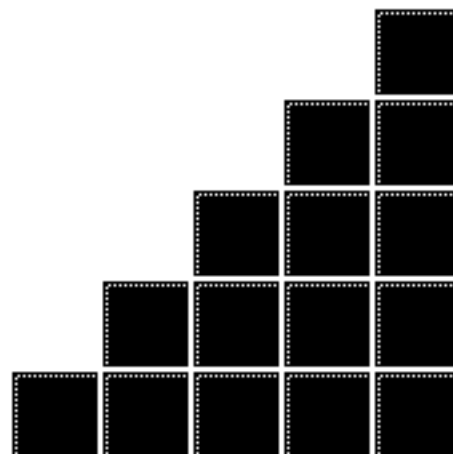
Li Huang

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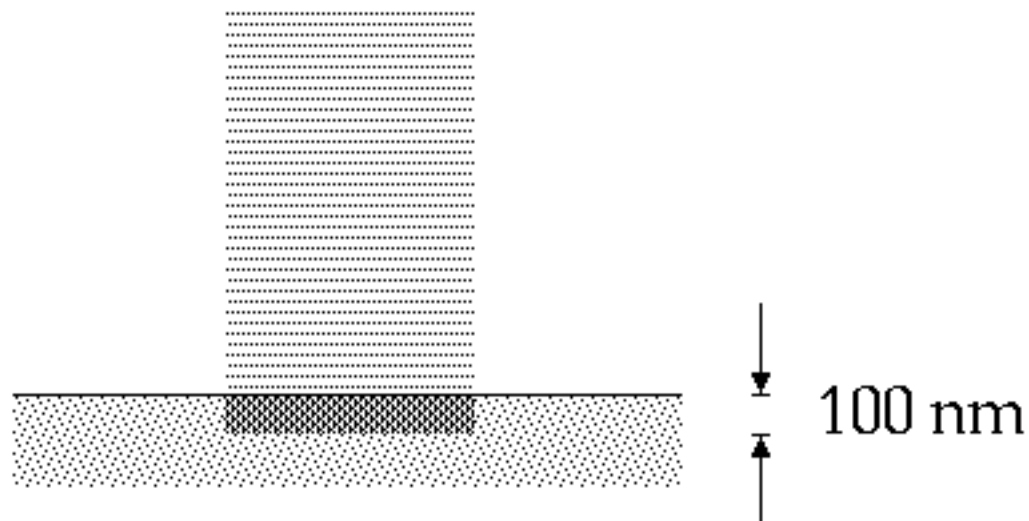*18 September 1996*

1976:   (nanosecond) laser annealing of
         crystals damaged by ion bombardment
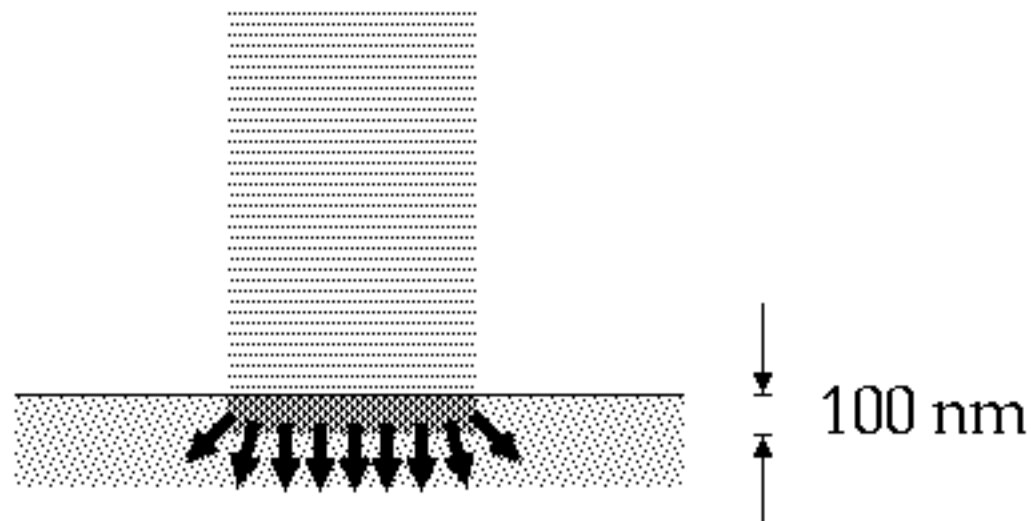
1985:   femtosecond laser 'melting' of Si

laser deposits energy near surface...

100 nm

energy rapidly diffuses into bulk...

100 nm

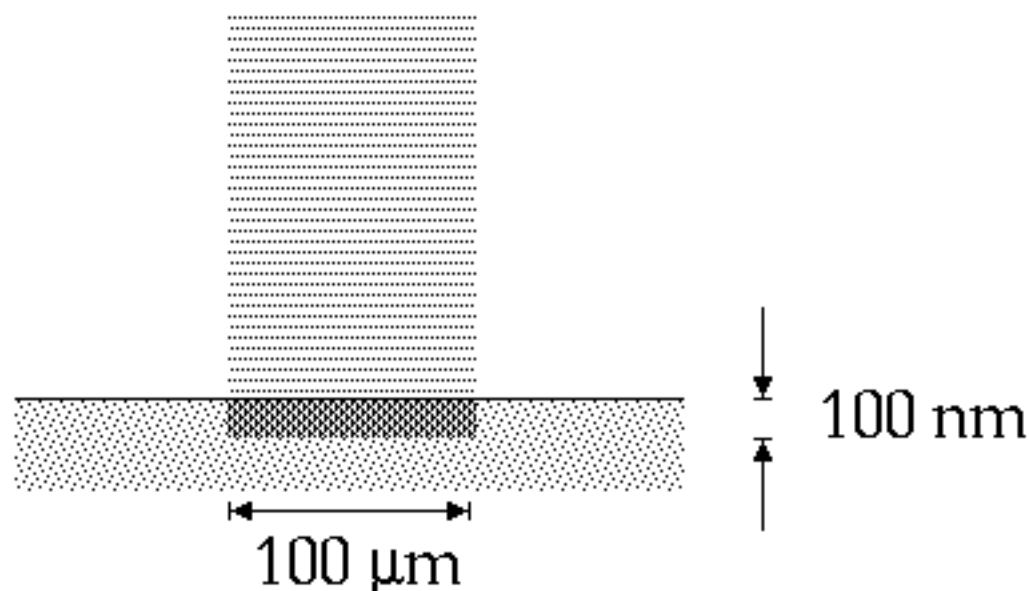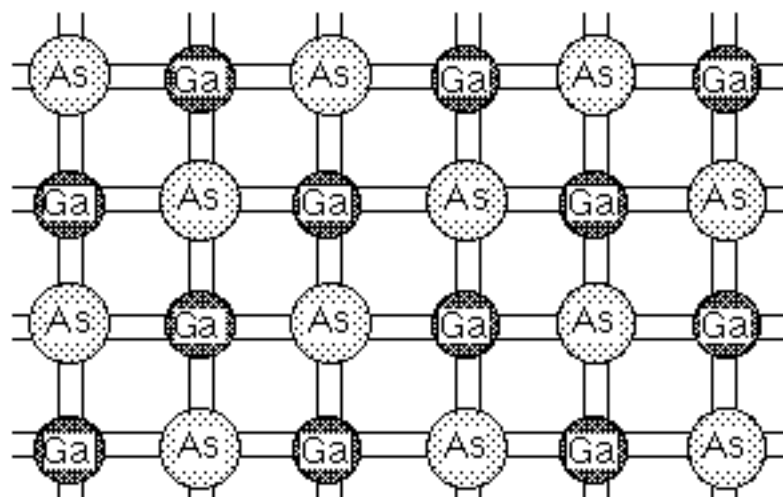in 1 ns, diffusion length ≈ 100 nm

For $t < 1$ ns can ignore diffusion

100 nm

100 μm

10 μJ into a volume of about 10^{-15} m^3 !

OUTLINE

① Background

② Single frequency work

③ Broadband work

how does light melt a solid?

photons excite valence electrons...

...and create hot electrons...
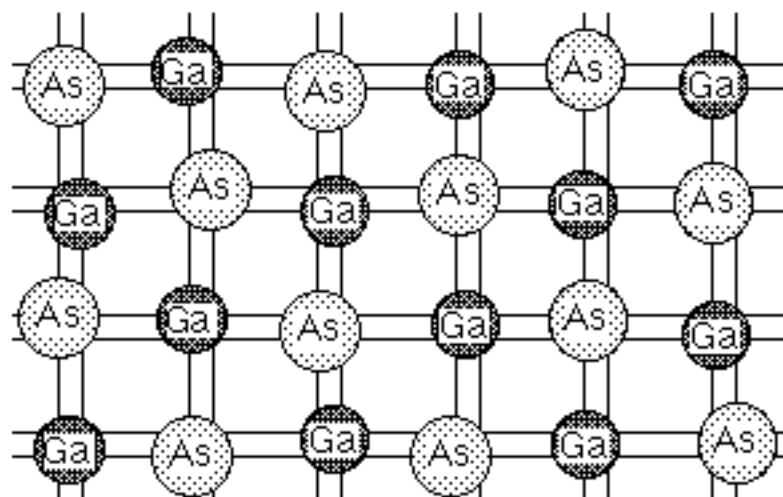
...which heat lattice

...which heat lattice

...which heat lattice

...or...

photons excite valence electrons...

...creating a dense plasma...

...and breaking bonds

CB

E

k

VB

CB

VB

photon excites valence electron

CB

VB

creating an electron-hole pair

CB

VB

multiphoton excitation

CB

VB

CB

VB

emission of LO phonons

CB

VB

emission of LO phonons

CB

VB

emission of LO phonons

CB

VB

emission of LO phonons

CB

VB

emission of LO phonons

emission of LO phonons

CB

VB

emission of LO phonons

CB

VB

emission of LO phonons

long pulses ($\tau_{exc} \gg 1$ ps):   *thermal melting*

photons

$\downarrow$

hot free electrons

$\downarrow$

hot phonons

$\downarrow$

melting

short pulses ($\tau_{exc} \ll 1$ ps):   *nonthermal disordering*

photons

$\downarrow$

hot free electrons

hot phonons

melting

❶ Background

❷ Single frequency work

❸ Broadband work

Phonons	How can we drive them?
Beyond phonons	What happens when we break the limit?

▶

EXCITATION OF PHONONS

absorption   incoherent heating $\tau_{e\text{-}ph} \approx 2\ \text{ps} \quad \gg \quad T_{ph}$

SRS, CARS   coherent driving $\tau_{exc} \geq 6\ \text{ps} \quad \gg \quad T_{ph}$

ISRS   impulsive excitation $\tau_{exc} \approx 0.1\ \text{ps} \quad \leq \quad T_{ph}$

▶

k_1 k_2

$$q$$

$$k_1 \qquad k_2$$

$$k_1 - k_2 = \pm q$$

create decaying standing wave...

create decaying standing wave...

create decaying standing wave...

create decaying standing wave...

create decaying standing wave...

create decaying standing wave...

create decaying standing wave...

create decaying standing wave...

IMPULSIVE RAMAN SCATTERING

create decaying standing wave...

Δt

...read out with third beam

Δt

...read out with third beam

LARGE AMPLITUDE OSCILLATIONS

10 pJ

Ti$_2$O$_3$

$\Delta R/R$

time (ps)

T.K. Cheng *et al., Appl. Phys. Lett.* **57** (1990) 1004
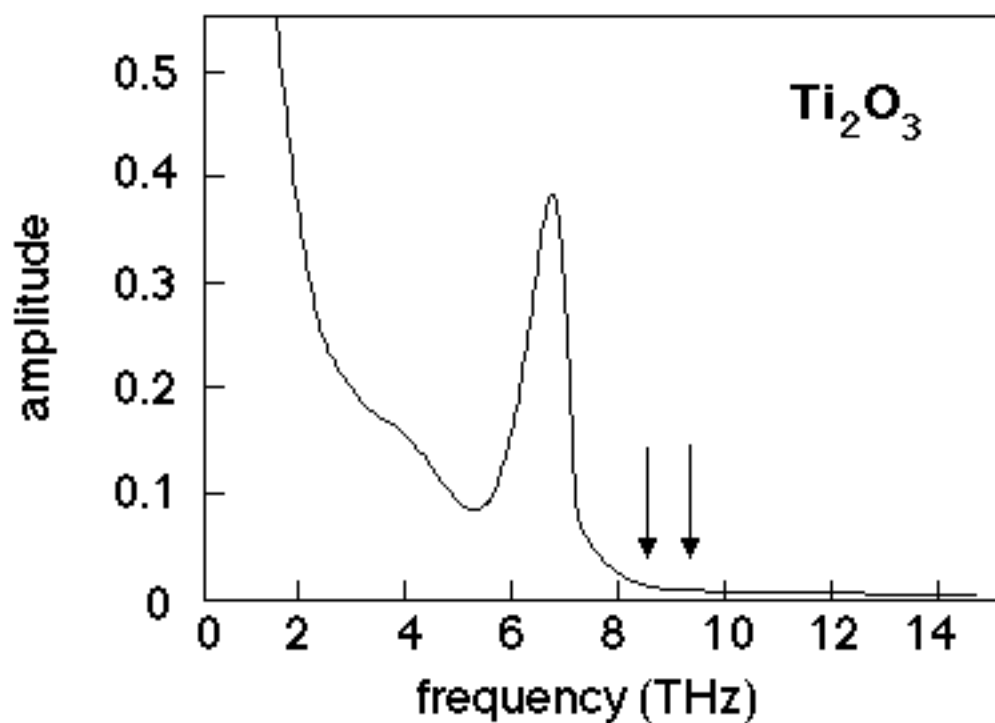
H.J. Zeiger *et al., Phys. Rev. B* **45** (1992) 768
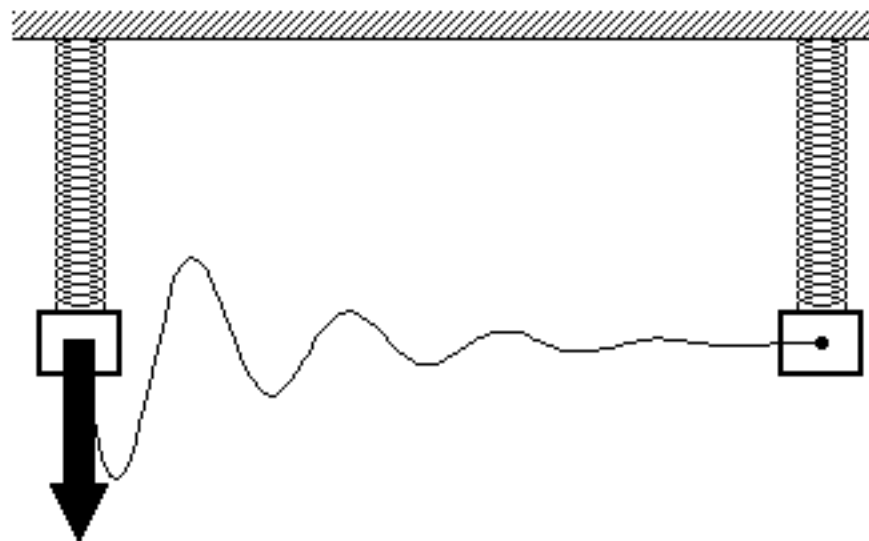
T.K. Cheng *et al.*, *Appl. Phys. Lett.* **57** (1990) 1004
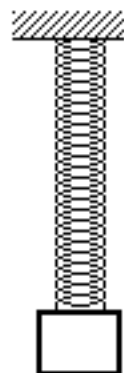
H.J. Zeiger *et al.*, *Phys. Rev. B* **45** (1992) 768

- need to match q
- sinusoidal oscillation

DISPLACIVE EXCITATION
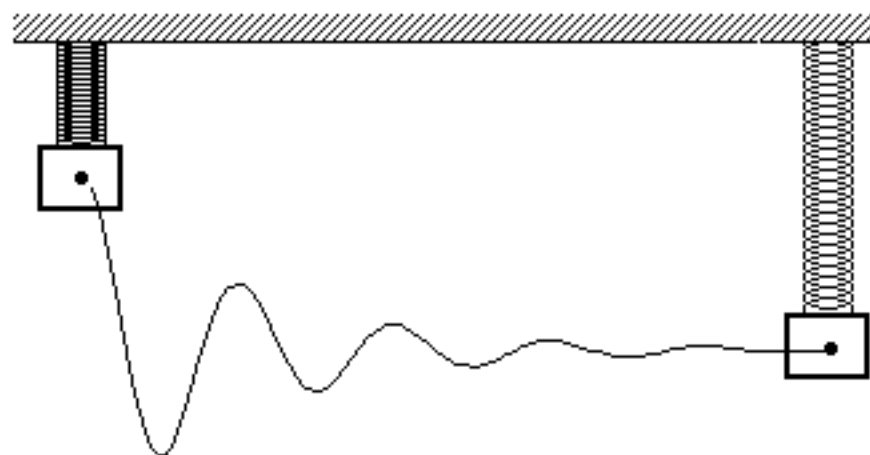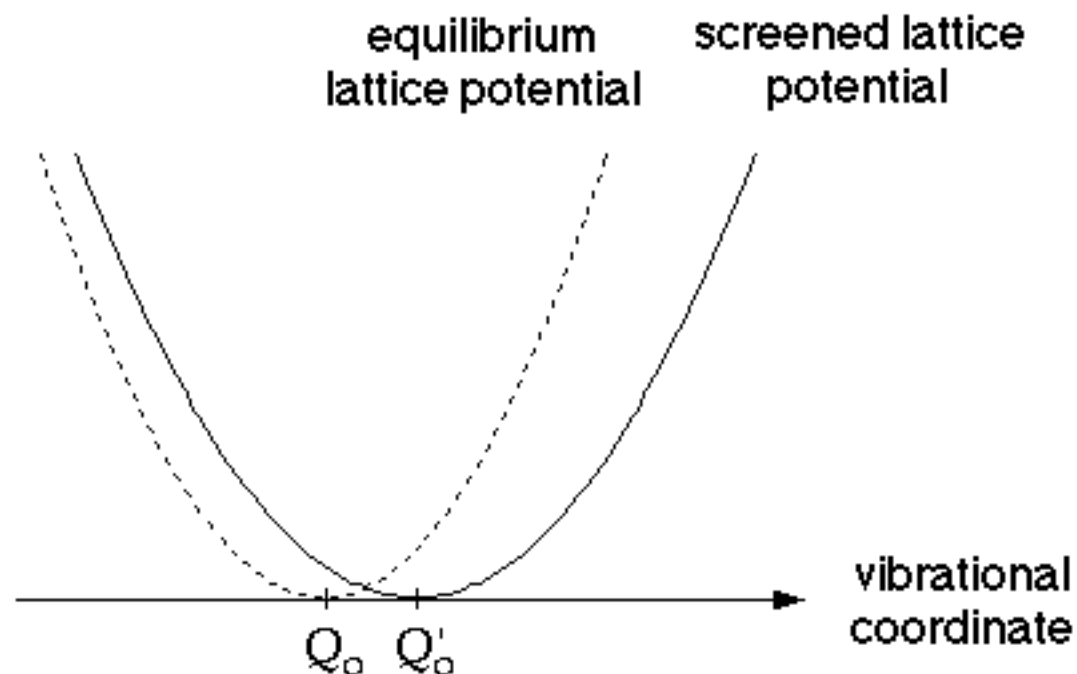
equilibrium
lattice potential

screened lattice
potential

vibrational
coordinate

Q_o Q_o'

10 nJ

$\Delta R/R$

Ti_2O_3

phonon frequency (THz)

Ti_2O_3

time (ps)

time (ps)

intense pulses can 'melt' GaAs, Si, but how?

CB

VB

(?)

CB

VB

intrinsic properties   measured properties

$\varepsilon\,',\varepsilon\,''(\omega)$ $\longrightarrow$ R

$\varepsilon\,',\varepsilon\,''(\omega)$
$\varepsilon\,',\varepsilon\,''(2\omega)$ $\longrightarrow$ SHG
$\chi_{(2)}$

▶

GaAs
(110)

pump

640 nm, 0.1 mJ

63°

probes

570 nm, 0.1 µJ

63°

all beams

70 fs, *p*-pol

63°

70.9°

R (70.9°)

R (75.8°)

Nd:YAG laser

amplifier

preamplifier

Ar-ion laser

CPM laser

Experiment

2.2 eV

0.4 kJ/m^2

Reε

Imε

dielectric constant

time (ps)

2.2 eV

2.2 eV

1.2 kJ/m^2

Imε

Reε

dielectric constant

time (ps)

2.2 eV

0.33 ps

Imε

Reε

dielectric constant

pump fluence (kJ/m^2)

2.2 eV

2.2 eV

Drude model:

$$\mathrm{Re}(\varepsilon) = 1 - \frac{Ne^2}{m\varepsilon_\circ}\frac{1}{\omega^2 + \gamma^2} \qquad \mathrm{Im}(\varepsilon) = \frac{Ne^2}{m\varepsilon_\circ}\frac{\gamma\omega}{\omega^4 + \gamma^2\omega^2}$$

ε

$\text{Im}\,\varepsilon$

$\text{Re}\,\varepsilon$

ω

ω_0

CB

VB

ω_0

semiconductor

$\omega_0 \approx 4.5 \text{ eV}$

CB

VB

$\omega_\circ$

semiconductor

ε ω_{probe}

$Im\varepsilon$

$Re\varepsilon$

ω

$\omega_\circ$

$\omega_{probe} = 2.2$ eV

semiconductor

pump pulse excites
valence electrons...

semiconductor

pump pulse excites
valence electrons...

semiconductor

pump pulse excites
valence electrons...

CB

ω_0

VB

semiconductor

ε ω_{probe}

Im ε

Re ε

ω

ω_0

pump pulse excites
valence electrons...

CB

ω_0

VB

semiconductor

ε ω_{probe}

$Im\,\varepsilon$

$Re\,\varepsilon$

ω

ω_0

pump pulse excites
valence electrons...

CB

$\omega_\circ$

VB

semiconductor

ε ω_{probe}

$Im\,\varepsilon$

$Re\,\varepsilon$

ω

$\omega_\circ$

pump pulse excites
valence electrons...

CB

VB

semiconductor

ε

ω_{probe}

$Im\,\varepsilon$

$Re\,\varepsilon$

ω

ω_0

pump pulse excites
valence electrons...

CB

VB

semiconductor

...and induces change
in bandstructure

ε ω_{probe}

ω

ω_0

CB

VB

semiconductor

...and induces change
in bandstructure

semiconductor

...and induces change
in bandstructure

ε

ω_{probe}

ω

ω_{o}

CB

VB

semiconductor

...and induces change
in bandstructure

CB

VB

semimetal

...and induces change
in bandstructure

metal

...and induces change
in bandstructure

CB

VB

ω_0

semiconductor

ε

ω_{probe}

Im ε

Re ε

ω

ω_0

ε

t

CB

$\omega_{\circ}$

VB

semiconductor

ε

ω_{probe}

Imε

Reε

ω

$\omega_{\circ}$

ε

t

CB

VB

ω_0

semiconductor

ε

ω_{probe}

Imε

Reε

ω

ω_0

ε

t

CB

VB

ω_0

semiconductor

ε

ω_{probe}

Imε

Reε

ω

ω_0

ε

t

CB

ω_0

VB

semiconductor

ε

ω_{probe}

Im ε

Re ε

ω

ω_0

ε

t

semiconductor

CB

VB

semiconductor

CB

VB

semiconductor

CB

VB

semiconductor

CB

VB

semiconductor

semiconductor

semimetal

CB

metal

GaAs BANDSTRUCTURE

GaAs

2.2 eV

energy (eV) vs wavevector (L, Λ, Γ, Δ, X)

S. Froyen *et al.*, *Phys Rev. B* **28** (1983) 3258

D.H. Kim *et al.*, *Sol. State. Comm.* **89** (1994) 119

GaAs BANDSTRUCTURE

GaAs DIELECTRIC FUNCTION

4.4 eV

0.33 ps

dielectric constant

Imε

Reε

pump fluence (kJ/m²)

4.4 eV

4.4 eV

4.4 eV

single-angle reflectivity not a
good indicator of what happens

laser pulse causes bandgap
collapse

2.2 eV

slow rise time → collapse cannot be caused by electronic effects alone

structural change?

Field strength at second harmonic:

$$E_r(2\omega) \;=\; -4\pi \, P^{(2)}(2\omega) \, g[\varepsilon(\omega), \; \varepsilon(2\omega), \; \theta_i]$$

Field strength at second harmonic:

$$E_\gamma(2\omega) = -4\pi\, P^{(2)}(2\omega)\, g[\varepsilon(\omega),\ \varepsilon(2\omega),\ \theta_i]$$

where:

$$P^{(2)}(2\omega) = 2\chi^{(2)} E_i^2(\omega)\, f[\varepsilon(\omega),\ \theta_i]$$

so:

Field strength at second harmonic:

$$E_r(2\omega) = -4\pi\, P^{(2)}(2\omega)\, g[\varepsilon(\omega),\ \varepsilon(2\omega),\ \theta_i]$$

where:

$$P^{(2)}(2\omega) = 2\chi^{(2)} E_i^2(\omega)\, f[\varepsilon(\omega),\ \theta_i]$$

so:

$$\left|\chi^{(2)}\right|^2 = \frac{E_r^2(2\omega)}{E_i^2(\omega)\ G[\varepsilon(\omega),\ \varepsilon(2\omega),\ \theta_i]}$$

▶

SECOND HARMONIC DATA

0.33 ps

G

pump fluence (kJ/m^2)

SECOND HARMONIC DATA

0.33 ps

$|\chi^{(2)}|^2$

pump fluence (kJ/m^2)

2.0 ps

$|\chi^{(2)}|^2$

pump fluence (kJ/m^2)

SECOND HARMONIC DATA

8.0 ps

$|\chi^{(2)}|^2$

pump fluence (kJ/m^2)

SECOND HARMONIC DATA

0.2 kJ/m^2

$\left|\chi^{(2)}\right|^2$

pump-probe time delay (ps)

$|\chi^{(2)}|^2$

0.2 kJ/m^2
0.4 kJ/m^2

pump-probe time delay (ps)

SECOND HARMONIC DATA

SECOND HARMONIC DATA

0.2 kJ/m^2
0.4 kJ/m^2

0.6 kJ/m^2

0.8 kJ/m^2

$|\chi^{(2)}|^2$

pump-probe time delay (ps)

SECOND HARMONIC DATA

$|\chi^{(2)}|^2$

pump-probe time delay (ps)

0.4 kJ/m^2

corrected

uncorrected

- $\chi^{(2)}$ sensitive to loss of long-range order

- long-range order disappears even below threshold

- structural change due to destabilization of covalent bonds

- time-scale for structural change reasonable (10% of bond length in 1 ps requires 25 m/s)

❶ Background

❷ Single frequency work

❸ Broadband work

▶

CaF$_2$

GaAs

spectrometer

CaF$_2$

GaAs

spatial filter

spectrometer

CaF$_2$

GaAs

spatial filter

spectral filter

spectrometer

CaF$_2$

GaAs

spatial filter

spectral filter

spectrometer

−16 ps

500 fs

1 ps

GaAs   0.45 F_{th}

2 ps

4 ps

4 ps

−16 ps

500 fs

1 ps

GaAs   0.70 F_{th}

2 ps

4 ps

4 ps

−16 ps

GaAs   1.6 F_{th}

500 fs

2 ps

4 ps

4 ps

GaAs   1.6 F_{th}

BROADBAND DATA

	short time	long time
low fluence		
medium fluence		
high fluence		

▶

BROADBAND DATA

	short time	long time
low fluence		
	electronic many-particle effects	
medium fluence		
high fluence		

▶

BROADBAND DATA

	short time	long time
low fluence	electronic many-particle effects	
medium fluence		
high fluence	structural effect?	

▶

BROADBAND DATA

	short time	long time
low fluence		hot lattice
	electronic many-particle effects	
medium fluence		
high fluence	structural effect?	

BROADBAND DATA

	short time	long time
low fluence		hot lattice
	electronic many-particle effects	
medium fluence		lattice disordering
high fluence	structural effect?	

▶

BROADBAND DATA

	short time	long time
low fluence	electronic many-particle effects	hot lattice
medium fluence		lattice disordering
high fluence	structural effect?	metallic behavior

▶

electronic excitation can drive phonons incoherently, coherently, or impulsively

electronic excitation can drive a structural transition

femtosecond lasers allow us to see the dynamics of the transition

http://mazur-www.harvard.edu